Low-power 3-input OR-AND gate Rev. 5 — 22 June 2012

Product data sheet

General description 1.

The 74AUP1G3208 provides the Boolean function: $Y = (A + B) \times C$. The user can choose the logic functions OR, AND and OR-AND. All inputs can be connected to V_{CC} or GND.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \,\mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power 3-input OR-AND gate

3. Ordering information

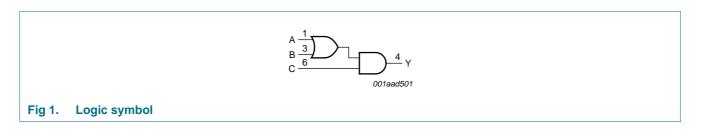
Table 1. Ordering	g information								
Type number	Package								
	Temperature range	Name	Description	Version					
74AUP1G3208GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363					
74AUP1G3208GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886					
74AUP1G3208GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891					
74AUP1G3208GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115					
74AUP1G3208GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202					

4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AUP1G3208GW	a2
74AUP1G3208GM	a2
74AUP1G3208GF	a2
74AUP1G3208GN	a2
74AUP1G3208GS	a2

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

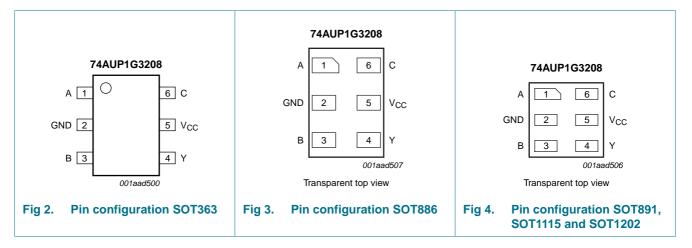
5. Functional diagram



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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
А	1	data input A
GND	2	ground (0 V)
В	3	data input B
Y	4	data output Y
V _{CC}	5	supply voltage
С	6	data input C

7. Functional description

Table 4. Function table^[1] Input Output С В Υ Α L L L L L L Н L Н L L L L Н Н L Н L L L Н Н L н Н Н L Н н н Н н

[1] H = HIGH voltage level; L = LOW voltage level.

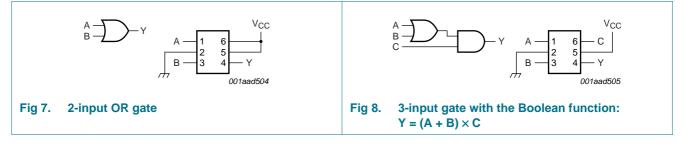
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7.1 Logic configurations

Table 5. Function selection table

Logic function	Figure
2-input AND	see Figure 5 and Figure 6
2-input OR	see Figure 7
3-input gate with the Boolean function: $Y = (A + B) \times C$	see Figure 8





8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 $^\circ$ C the value of P_{tot} derates linearly with 4.0 mW/K.

For XSON6 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

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Recommended operating conditions 9.

Table 7.	Recommended operating conditi	ons			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	0	200	ns/V

10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 imes V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 imes V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 imes V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		I_{O} = 20 µA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 imes V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V

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Table 8. At recom	Static characteristics mended operating conditions	continued ; voltages are referenced to GND (ground :	= 0 V).			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
li -	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I _{OFF}	power-off leakage current	$V_{\rm I}~{\rm or}~V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V	-	-	±0.2	μA
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μΑ
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
ΔI_{CC}	additional supply current		-	-	40	μΑ
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.8	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.7	-	pF
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 imes V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 0.8 \ \text{V} \text{ to } 3.6 \ \text{V}$	V _{CC} – 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	$0.7 imes V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I _I	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μA
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μA
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA

Table 8. Static characteristics ...continued

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
lcc	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	0.9	μA
∕l ^{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	50	μA
T _{amb} = –	40 °C to +125 °C					
√ _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.75 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
/ _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
√ _{ОН}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	V _{CC} – 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 imes V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_0 = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
/ _{OL}	LOW-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		$I_{O} = 20 \ \mu$ A; $V_{CC} = 0.8 \ V$ to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 imes V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μA
OFF	power-off leakage current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6 V; $V_{\rm CC} = 0$ V	-	-	±0.75	μΑ
	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μΑ
СС	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
7I ^{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

Table 8. Static characteristics ...continued

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions		25 °C		–40 °C to +125 °C			Uni
			Min	Typ[1]	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F		1						
^t pd	propagation delay	A, B or C to Y; see Figure 9	[2]						
		$V_{CC} = 0.8 V$	-	18.5	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	2.2	5.4	10.6	2.2	10.9	11.1	ns
		V_{CC} = 1.4 V to 1.6 V	1.9	3.8	6.4	1.8	6.9	7.2	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	3.1	5.1	1.4	5.6	5.9	ns
		V_{CC} = 2.3 V to 2.7 V	1.3	2.4	3.7	1.2	4.1	4.4	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.2	2.2	3.2	1.1	3.4	3.6	ns
C _L = 10	pF								
t _{pd}	propagation delay	A, B or C to Y; see Figure 9	[2]						
		$V_{CC} = 0.8 V$	-	22.1	-				ns
		V_{CC} = 1.1 V to 1.3 V	2.6	6.3	12.4	2.5	12.8	13.1	ns
		V_{CC} = 1.4 V to 1.6 V	2.3	4.4	7.4	2.1	8.0	8.4	ns
		V_{CC} = 1.65 V to 1.95 V	2.0	3.6	5.9	1.8	6.4	6.8	ns
		V_{CC} = 2.3 V to 2.7 V	1.7	3.0	4.4	1.6	4.8	5.1	ns
		V_{CC} = 3.0 V to 3.6 V	1.6	2.7	3.9	1.4	4.2	4.4	ns
C _L = 15	pF								
t _{pd}	propagation delay	A, B or C to Y; see Figure 9	[2]						
		$V_{CC} = 0.8 V$	-	25.6	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	3.0	7.1	14.1	2.8	14.6	14.9	ns
		V_{CC} = 1.4 V to 1.6 V	2.6	5.0	8.4	2.4	9.1	9.5	ns
		V_{CC} = 1.65 V to 1.95 V	2.2	4.1	6.7	2.1	7.4	7.8	ns
		V_{CC} = 2.3 V to 2.7 V	2.0	3.4	5.0	1.9	5.5	5.9	ns
		V_{CC} = 3.0 V to 3.6 V	1.9	3.2	4.5	1.7	4.8	5.0	ns
C _L = 30	pF								
t _{pd}	propagation delay	A, B or C to Y; see Figure 9	[2]						
		$V_{CC} = 0.8 V$	-	34.1	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	3.9	9.3	18.9	3.7	19.7	20.1	ns
		V_{CC} = 1.4 V to 1.6 V	3.4	6.5	11.0	3.2	12.1	12.7	ns
		V_{CC} = 1.65 V to 1.95 V	3.0	5.4	8.9	2.9	9.7	10.3	ns
		V_{CC} = 2.3 V to 2.7 V	2.8	4.5	6.5	2.6	7.1	7.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.6	4.3	5.8	2.4	6.4	6.7	ns

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Voltages	are referenced to G	ND (ground = 0 V); for test circuit see	Figure	<u>10</u> .					
Symbol	Parameter	Conditions	25 °C		–40 °C to +125 °C			Unit	
				Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F, 10 pF, 15 pF and	30 pF							
C _{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_1 = \text{GND to } V_{\text{CC}}$ [3][4]							
		$V_{CC} = 0.8 V$	-	2.6	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	2.7	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	-	2.8	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	-	3.0	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	3.5	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	4.0	-	-	-	-	pF

Table 9. Dynamic characteristics ... continued

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] All specified values are the average typical values over all stated loads.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

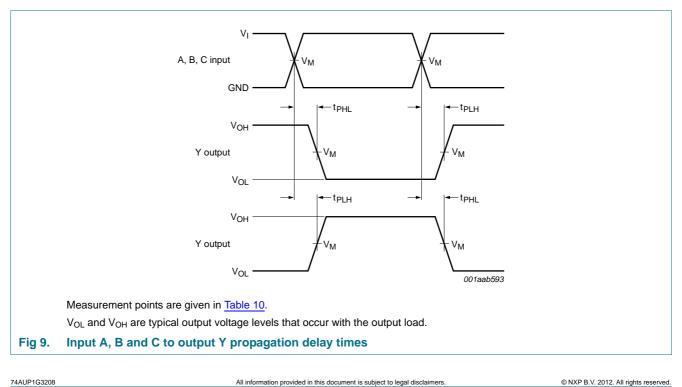
 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



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Measurement points

Table 10.

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Supply voltage	Output	Input						
V _{CC}	V _M	V _M	VI	t _r = t _f				
0.8 V to 3.6 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{CC}	≤ 3.0 ns				
	$\begin{array}{c} G \\ G \\ \hline \\$							
		00	1aac521					
Test data is given in T	<u>able 11</u> .							
Definitions for test cire	cuit:							
R_L = Load resistance.								
C _L = Load capacitanc	e including jig and probe c	apacitance.						
R _T = Termination resis	stance should be equal to	the output impedance Z _o o	f the pulse generator.					

 V_{EXT} = External voltage for measuring switching times.

Fig 10. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 M\Omega$.

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13. Package outline

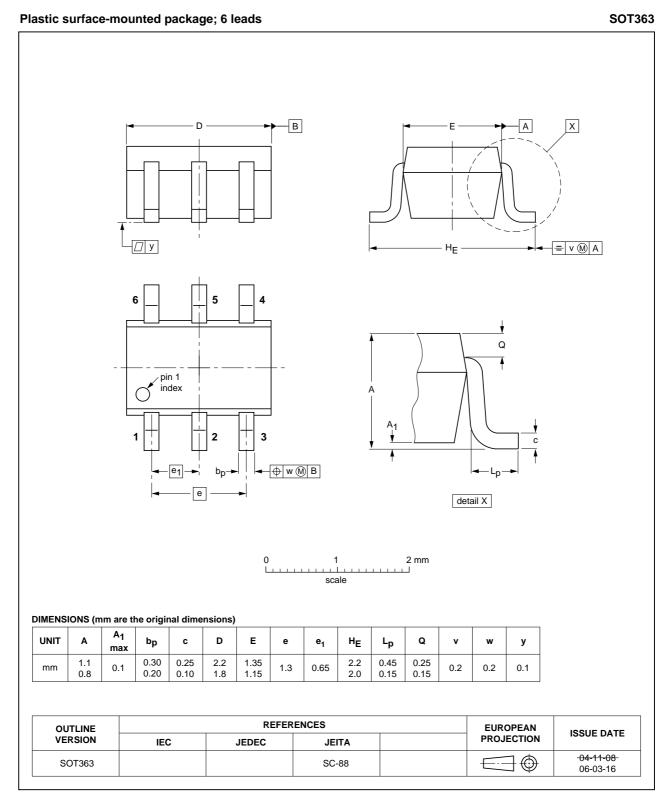


Fig 11. Package outline SOT363 (SC-88)

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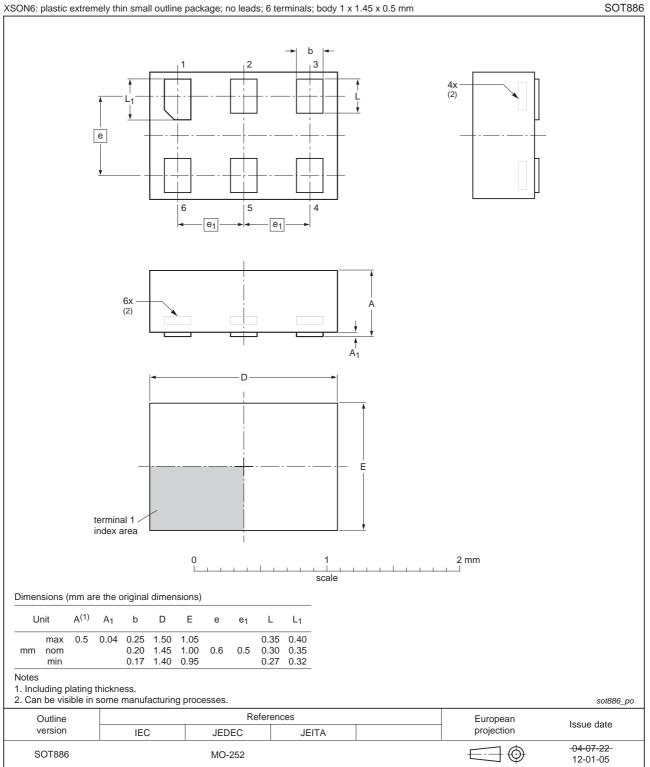


Fig 12. Package outline SOT886 (XSON6)

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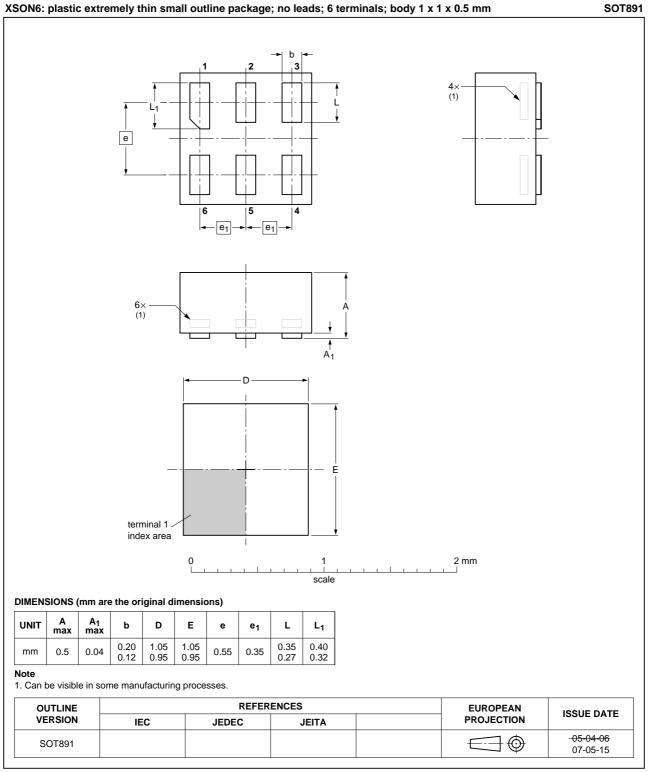
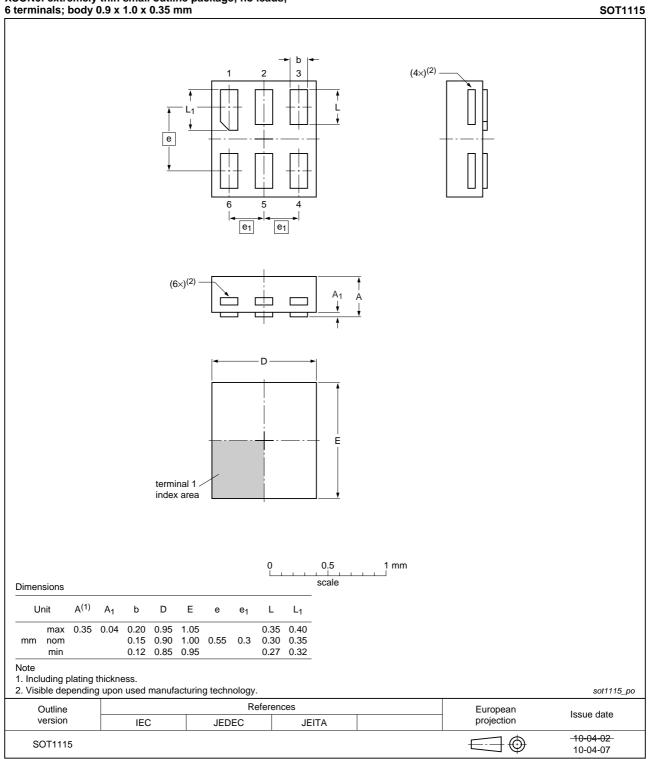


Fig 13. Package outline SOT891 (XSON6)

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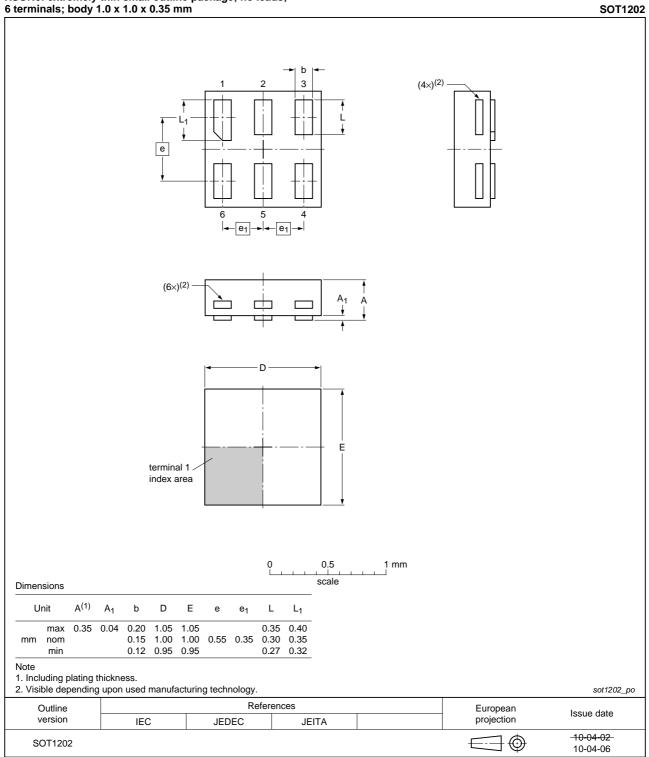
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XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1115 (XSON6)

Low-power 3-input OR-AND gate



XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 15. Package outline SOT1202 (XSON6)

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14. Abbreviations

Table 12. Abbreviations		
Acronym	Description	
CDM	Charged Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	

15. Revision history

Table 13.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G3208 v.5	20120622	Product data sheet	-	74AUP1G3208 v.4
Modifications:	 Package ou 	tline drawing of SOT886 (F	igure 12) modified.	
74AUP1G3208 v.4	20111123	Product data sheet	-	74AUP1G3208 v.3
Modifications:	 Legal pages 	s updated.		
74AUP1G3208 v.3	20101011	Product data sheet	-	74AUP1G3208 v.2
74AUP1G3208 v.2	20090703	Product data sheet	-	74AUP1G3208 v.1
74AUP1G3208 v.1	20061129	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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